L Number	Hits	Search Text	DB	Time stamp
1	1	("6143476").PN.	USPAT	2004/11/06 14:26
-	359125	438/$.ccls. or 257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:35
-	1082	(438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:37
-	635	((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:38
-	401	(((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))) and interconnect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:38
-	42	((((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))) and interconnect$3) and (blanket near5 (insulat$3 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:57
-	2	(((((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))) and interconnect$3) and (blanket near5 (insulat$3 or dielectric))) and ((tungsten or W) same (bitline or (bit adj2 line)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:40
-	14	(((((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))) and interconnect$3) and (blanket near5 (insulat$3 or dielectric))) and (bitline or (bit adj2 line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 21:42
-	40	((((((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))) and interconnect$3) and (blanket near5 (insulat$3 or dielectric))) not ((((((438/$.ccls. or 257/$.ccls.) and ((hard adj mask$3) same (third or multiple or multilayer$2))) and ((etch$3 or pattern$3) near5 (metal or conductor or wir$3))) and interconnect$3) and (blanket near5 (insulat$3 or dielectric))) and ((tungsten or W) same (bitline or (bit adj2 line))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/06 14:26